

INTRODUCE:

HVGT high voltage silicon rectifier diodes is made of high quality glass passivated chip and high reliability epoxy resin sealing structure, and through professional testing equipment inspection qualified after to customers.

FEATURES:

1. High reliability design.
2. High voltage design.
3. High frequency .
4. Conform to RoHS.
5. Epoxy resin molded in vacuumHave anticorrosion in the surface.

APPLICATIONS:

1. High voltage multiplier circuit
2. Electrostatic generator circuit .
3. General purpose high voltage rectifier.
4. Other.

MECHANICAL DATA:

1. Case: epoxy resin molding.
2. Terminal: welding axis.
3. Net weight: 0.28 grams (approx).

SHAPE DISPLAY:

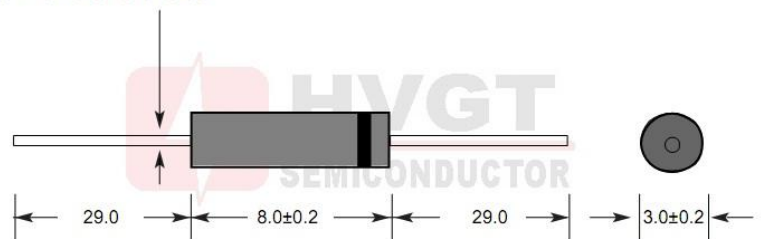


SIZE: (Unit:mm)

HVGT NAME: DO-308

DO-308 Series

Lead Diameter 0.6±0.03



Unit:mm

MAXIMUM RATINGS AND CHARACTERISTICS: (Absolute Maximum Ratings)

Items	Symbols	Condition	Data Value	Units
Repetitive Peak Reverse Voltage	V_{RRM}	$T_A=25^{\circ}C$	4.0	kV
Average Forward Current Maximum	I_{FAVM}	$T_A=25^{\circ}C$	200	mA
		$T_{OIL}=-^{\circ}C$	--	mA
Surge Current	I_{FSM}	$T_A=25^{\circ}C$; Half-Sine Wave; 8.3mS	10	A
Junction Temperature	T_J		-40~+125	$^{\circ}C$
Allowable Operation Case Temperature	T_c		125	$^{\circ}C$
Storage Temperature	T_{STG}		-40~+125	$^{\circ}C$

ELECTRICAL CHARACTERISTICS: $T_A=25^{\circ}C$ (Unless Otherwise Specified)

Items	Symbols	Condition	Data value	Units
Maximum Forward Voltage Drop	V_F	at $25^{\circ}C$; at $I_{F(AV)}$	13	V
Maximum Reverse Current	I_{R1}	at $25^{\circ}C$; at V_{RRM}	2.0	μA
	I_{R2}	at $100^{\circ}C$; at V_{RRM}	20	μA
Maximum Reverse Recovery Time	T_{RR}	at $25^{\circ}C$; $I_F=0.5I_R$; $I_R=I_{FAVM}$; $I_{RR}=0.25I_R$	100	nS
Junction Capacitance	C_J	at $25^{\circ}C$; $V_R=0V$; $f=1MHz$	15	pF



Fig 1

Forward Current Derating Curve

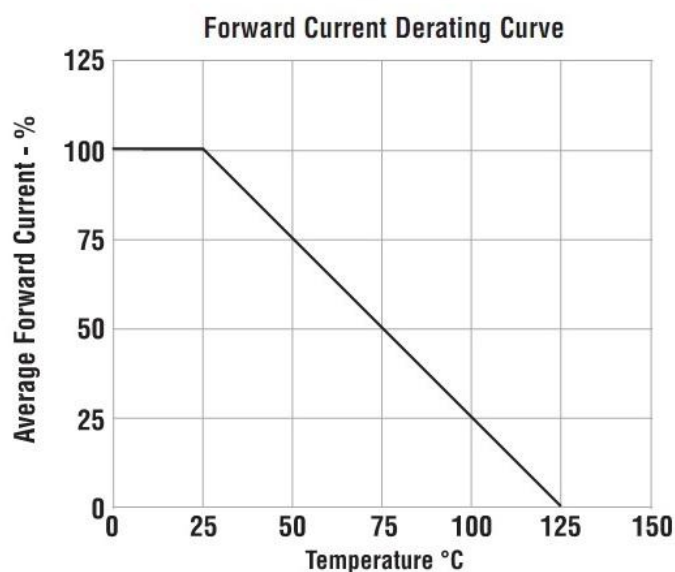


Fig 2

Reverse Recovery Measurement Waveform

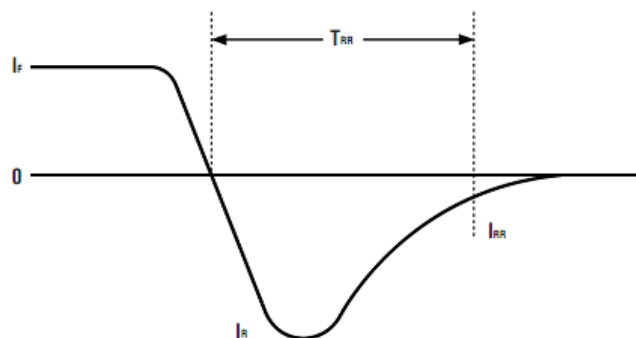
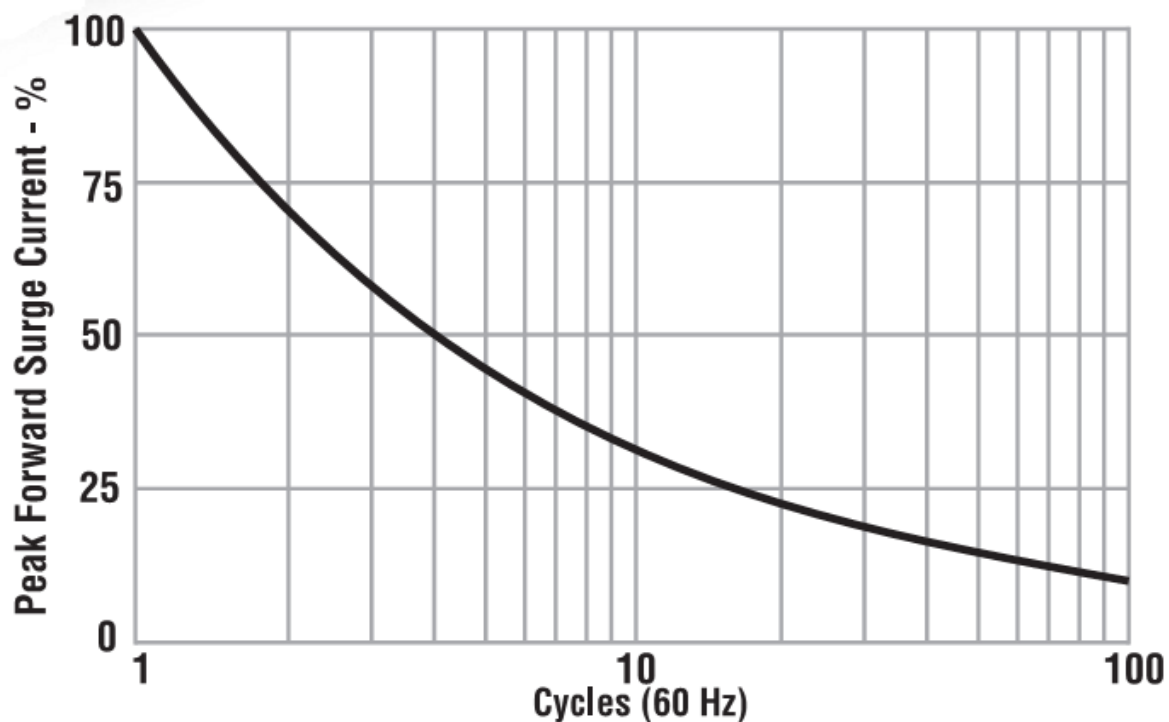


Fig 3

Non-Repetitive Surge Current



Marking

Type

2CL2FD

Code

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Cathode Mark

